### **Innogration**

## **GaN Power Amp Pallet**

## GMPA6472-75H



**Product Features** 

**Applications** 

6.4-7.2GHz(C band)

5G Power amplifier

75W Pulsed CW or CW

C band Satcom

50% Drain Efficiency@28V

ISM

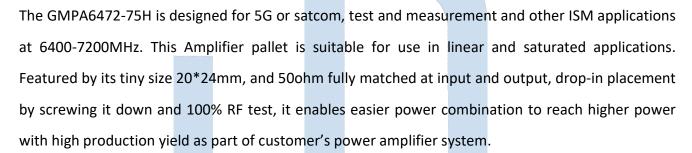
50ohm in and out, 20\*24mm, screw down

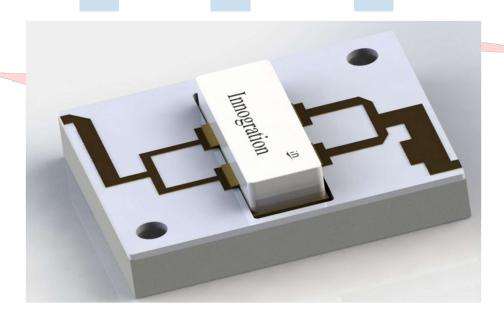
Point to point

Linear or saturated use

Radio link

### **Description**





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## Electrical Specifications @VCC=28V, T=25°C, 50Ωsystem

PARAMETER	UNIT	MIN	ТҮР	MAX	SYMBOL
Operating Frequency	MHz	6400	-	7200	fo
Operating Bandwidth	MHz	800		-	OBW
Pulse CW Output Power	W	75	80	-	Pout
Power Gain	dB	7	8	-	G <sub>P</sub>
Gain Flatness	dB	-	±0.75	-	$G_{F}$
Input Return Loss	dB	-	-	-10	S <sub>11</sub>
Operating Voltage	V	-	28	36	$V_{DS}$
Quiescent Current	mA	-	100	-	I <sub>DQ</sub>
Efficiency@Psat	%		50	-	Eff

### **Environmental Characteristics**

PARAMETER	UNIT	MIN	ТҮР	MAX	SYMBOL
Operating Case Temperature	$^{\circ}$	-20	-	85	Та
Storage Temperature	$^{\circ}$	-40		100	Tstg
Relative humidity w/o condensation	%	-	-	95	RH

## **Mechanical Specifications**

PARAMETER	UNIT	VALUE
Dimensions(L × W × H)	mm	20×24×4
Weight	g	50
RF Input Connector	-	N/A
RF Output Connector	-	N/A
Cooling	-	External Heat-sink

## **GaN Power Amp Pallet**

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## **Typical performance**

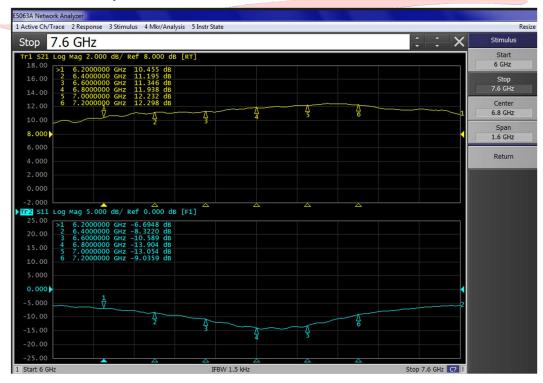
• Pulsed CW performance: Vds=+28V, IDQ=100mA, T=25°C, pulse width 100us, duty cycle 10%,

Freq(MHz)	Pin(dBm)	PoutdBm)	Pout(W)	IDS(A)	Gain(dB)	Eff(%)
6400	41.75	49.53	89.74	0.65	7.78	49.31
6500	41.32	50	100.00	0.7	8.68	51.02
6600	40.54	49.87	97.05	0.67	9.33	51.73
6700	42.06	49.88	97.27	0.67	7.82	51.85
6800	40.95	50.02	100.46	0.69	9.07	52.00
6900	40.87	49.56	90.36	0.63	8.69	51.23
7000	41.62	49.55	90.16	0.6	7.93	53.66
7100	40.73	49.68	92.90	0.62	8.95	53.51
7200	41.73	49.2	83.18	0.57	7.47	52.12

CW performance: Vds=+28V, IDQ=100mA, T=25℃

Freq(MHz)	Pin(dBm)	PoutdBm)	Pout(W)	IDS(A)	Gain(dB)	Eff(%)
6400	42.15	49.15	82.22	6.16	7	47.67
6500	41.59	49.68	92.90	6.84	8.09	48.50
6600	40.81	49.47	88.51	6.49	8.66	48.71
6700	42.17	49.47	88.51	6.4	7.3	49.39
6800	41.04	49.67	92.68	6.71	8.63	49.33
6900	40.78	49.11	81.47	5.93	8.33	49.07
7000	41.53	49.2	83.18	5.83	7.67	50.95
7100	40.61	49.42	87.50	6.16	8.81	50.73
7200	41.5	48.85	76.74	5.39	7.35	50.85

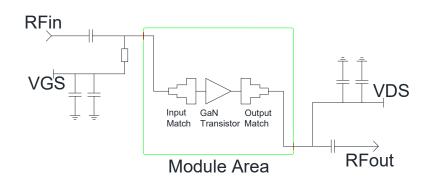
S21/S11 from network analyzer VDS=28V VGS=-3.23V IDQ=400mA

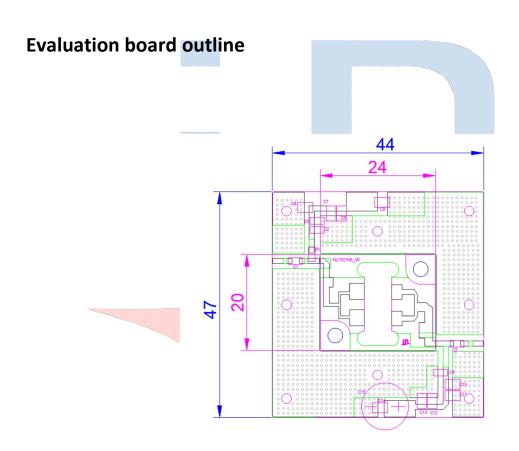


## GMPA6472-75H



## **Evaluation board Block Diagram**





Component	Description	Suggestion	
C1、C2、C3、C4	2.4pF	DLC75D	
C5	100pF	DLC75D	
C6-C14	Ceramic multilayer capacitor, 10uF, 100V	10uF/100V	
C15	470UF	63V/470UF	
R1	Chip Resistor,10 Ω ,0805		
PCB	3.508mm 1/0oz TACONIC RF-35TC-0200-A-CL1/C3mm		

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#### **Revision History**

**Document revision history** 

Date	Revision	Datasheet Status
2023/02/09	Rev 1.0	Preliminary Datasheet

Application data based on YHG-23-03 (NL7507HS)



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